

20V N-Channel MOSFETs

General Description

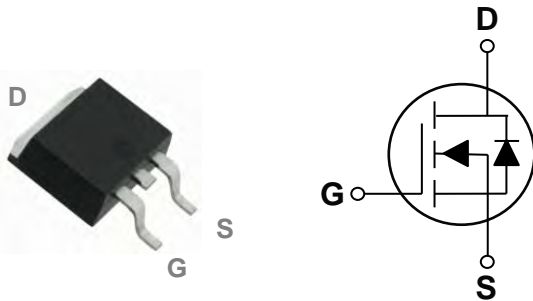
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
20V	17mΩ	30A

Features

- 20V,30A, $R_{DS(ON)} = 17m\Omega @ V_{GS} = 4.5V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

TO-252 Pin Configuration



Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 16	V
I_D	Drain Current – Continuous (Chip Limitation, $T_c=25^\circ\text{C}$)	30	A
	Drain Current – Continuous (Chip Limitation, $T_c=100^\circ\text{C}$)	19	A
I_{DM}	Drain Current – Pulsed ¹	120	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	24.9	W
	Power Dissipation – Derate above 25°C	0.20	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	5.02	$^\circ\text{C}/\text{W}$



FTK2612AD

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Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Static State Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25 °C, I _D =1mA	---	0.015	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =20V, V _{GS} =0V, T _J =25 °C	---	---	1	uA
		V _{DS} =16V, V _{GS} =0V, T _J =125 °C	---	---	10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±16V, V _{DS} =0V	---	---	±100	nA
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =10A	---	14	17	mΩ
		V _{GS} =2.5V, I _D =5A	---	18.5	24	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.5	0.8	1.2	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-2.76	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =5A	---	14	---	S

Dynamic Characteristics

Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =4.5V, I _D =5A	---	5.9	12	nC
Q _{gs}	Gate-Source Charge		---	0.7	2	
Q _{gd}	Gate-Drain Charge		---	1.8	4	
T _{d(on)}	Turn-On Delay Time	V _{DD} =10V, V _{GS} =4.5V, R _G =3.3Ω I _D =1A	---	4.8	10	ns
T _r	Rise Time		---	7.5	15	
T _{d(off)}	Turn-Off Delay Time		---	16.5	32	
T _f	Fall Time		---	4.8	10	
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, F=1MHz	---	775	1440	pF
C _{oss}	Output Capacitance		---	95	190	
C _{rss}	Reverse Transfer Capacitance		---	58	120	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	2.2	---	Ω

Drain - Source Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	30	A
I _{SM}	Pulsed Source Current ²		---	---	60	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25 °C	---	---	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

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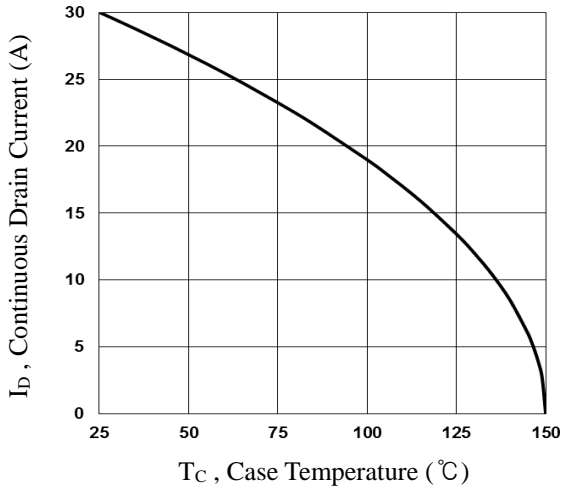


Fig.1 Continuous Drain Current vs. T_c

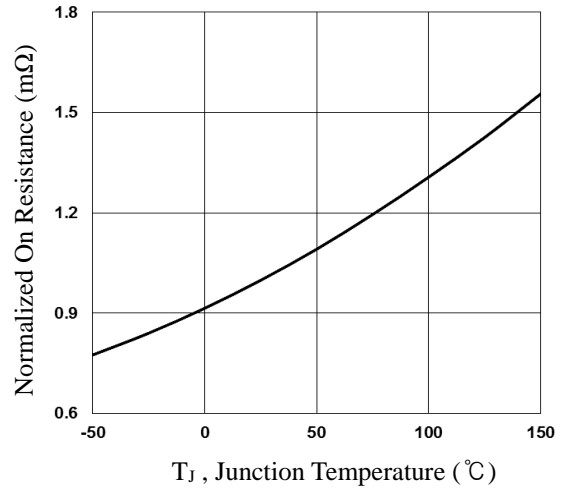


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

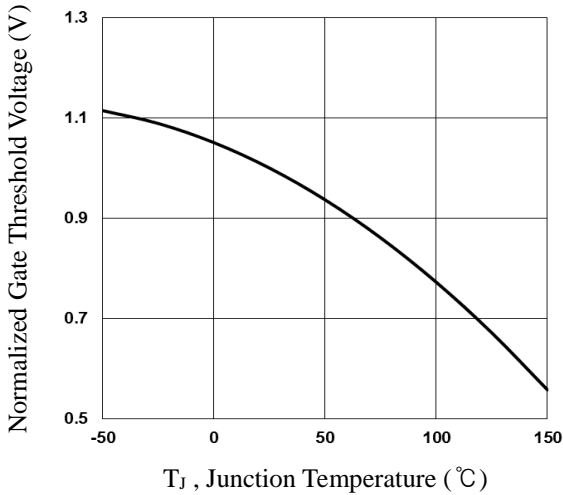


Fig.3 Normalized V_{th} vs. T_j

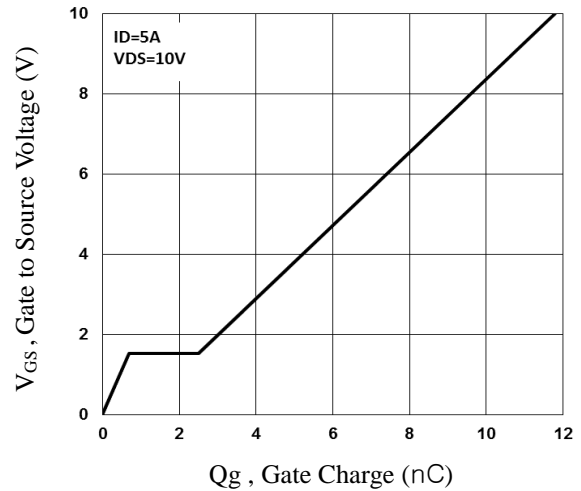


Fig.4 Gate Charge Waveform

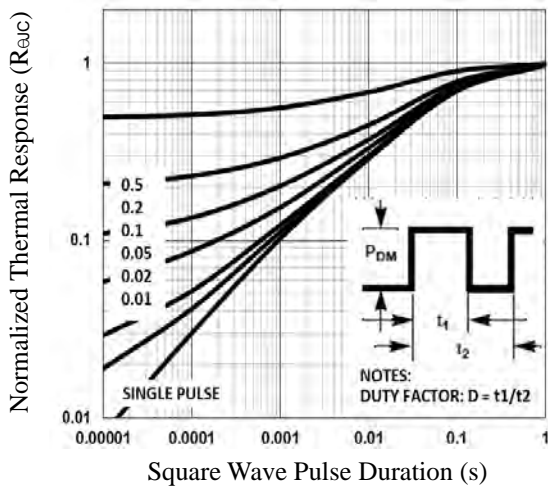


Fig.5 Normalized Transient Impedance

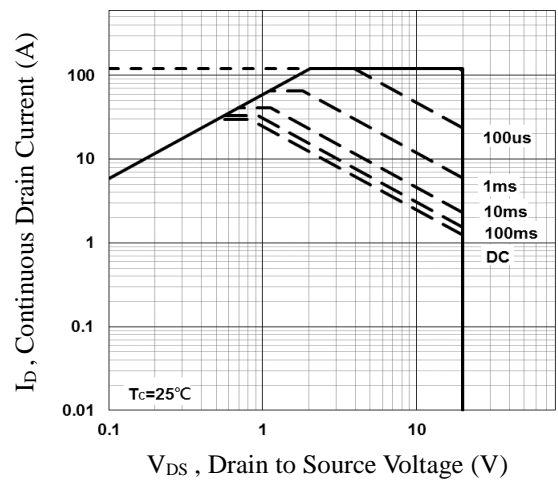


Fig.6 Maximum Safe Operation Area

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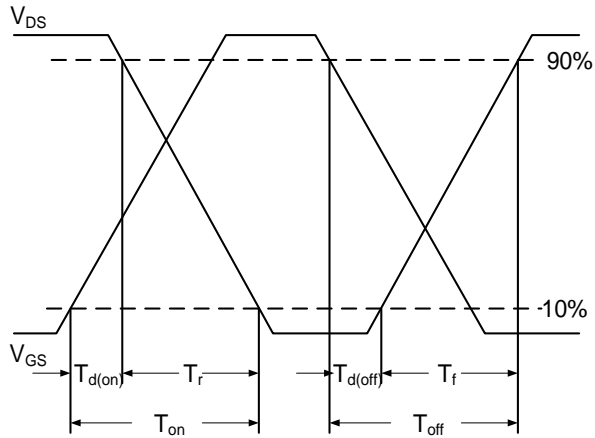


Fig.7 Switching Time Waveform

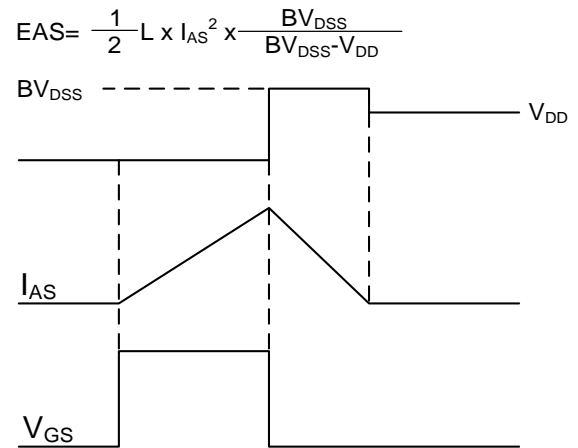
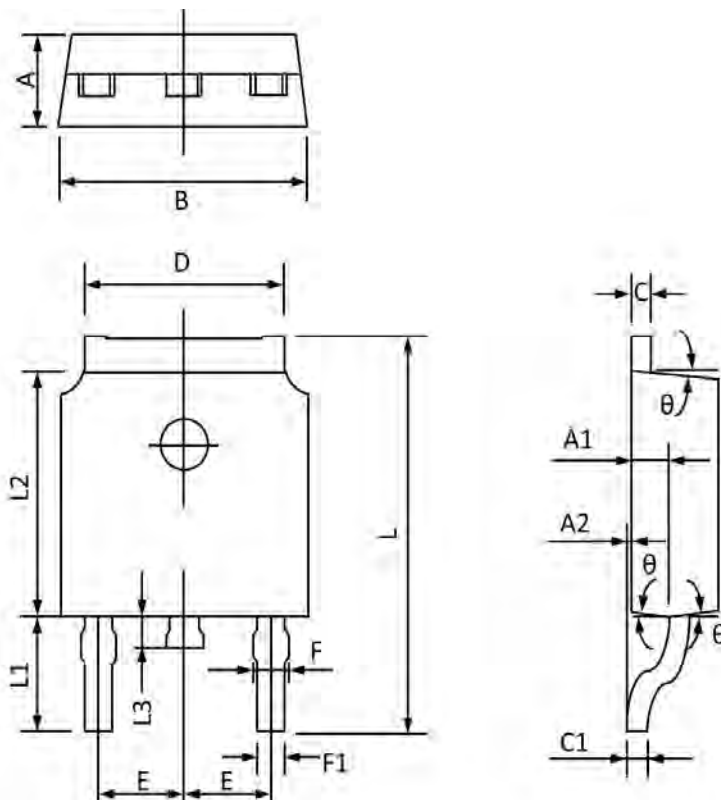


Fig.8 EAS Waveform

TO-252 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	2.400	2.200	0.094	0.087
A1	1.110	0.910	0.044	0.036
A2	0.150	0.000	0.006	0.000
B	6.800	6.400	0.268	0.252
C	0.580	0.450	0.023	0.018
C1	0.580	0.460	0.023	0.018
D	5.500	5.100	0.217	0.201
E	2.386	2.186	0.094	0.086
F	0.940	0.600	0.037	0.024
F1	0.860	0.500	0.034	0.020
L	10.400	9.400	0.409	0.370
L1	3.000	2.400	0.118	0.094
L2	6.200	5.400	0.244	0.213
L3	1.200	0.600	0.047	0.024
θ	9°	3°	9°	3°